# Output Prediction Logic: A High Performance CMOS Design Technique 

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## Outline

- Background
- Why static CMOS is slow
- Output Prediction Logic (OPL)
- OPL clocking
- Single-rail results: TSMC 0.25 um process
- OPL-differential logic
- Results for TSMC 0.18um process
- Robustness with PVT variations and noise
- World's fastest 64b adder
- Conclusion


## Background

- Dynamic circuit families such as domino are commonly used in today's high-performance microprocessors
- Increased performance due to:
- reduced input capacitance
- lower switching thresholds
- fewer levels of logic (due to the use of wide gates)
- Dynamic logic yields average speed improvement of $60 \%$ over static CMOS for random logic blocks
- when using synthesis tools tailored specifically for dynamic logic
- Dual rail domino, DS domino, Monotonic Static, CD domino


## Background (cont'd)

- Dynamic circuits have notable disadvantages
- Domino logic must be mapped to a unate network, which usually requires duplication of logic
- Main disadvantage going forward: increased noise sensitivity (compared to static CMOS)
- Increase noise margin: sacrifice performance gain
- Elusive goal: retain the good attributes of static CMOS (high noise immunity and easy technology mapping) while obtaining greater speed


## Why Static CMOS is So Slow

- All gates are inherently inverting
- On any circuit path, in the worst case:
- Every output must fully transition from 1 to 0 , or 0 to 1
- You must design for the worst case



## Output Prediction Logic

- Goal: reduce the worst case
- Assume all outputs on a critical path will be 1
- You will be correct EXACTLY half the time
- Every other gate on the path will not have to make ANY transition
- Critical path delay will be reduced by at least $50 \%$



## Output Prediction Logic

- Problem:
- 1 at every output (and therefore input) is not a stable state for an inverting gate
- The 1 will erode (possibly going to 0 ) in the latter gates of a critical path
- Solution:
- Disable each gate (1 at inputs and a 1 output is no longer a contradiction)
- Disable each gate until its inputs are ready for evaluation
- Predicted output value is therefore maintained


## OPL-Static CMOS NOR3



## OPL Pseudo-nMOS Gate

- Tri-state, pre-charge high inverting gate
- Size of pull-up device has small impact on delay
- Reasonable delays with increasing pull-down stack height



## OPL-Dynamic NOR3



## OPL Clocking



## Chain of 3 OPL-Static NOR3's



## OPL Clocking

- When a clock arrives after inputs have settled:



## OPL Clocking (cont'd)

- When a clock arrives BEFORE inputs have settled:



## Optimal OPL Clocking

- Consider a gate whose (controlling) input goes low: output should remain 1



## Delay vs. Clock Separation for OPL-Static NOR3 Chain



## Waveforms for OPL NOR3 Chain



## OPL Clocking for General Circuits

- Levelize the circuit
- Each level gets its own clock phase
- May have to add a buffer (two inverters) if a signal jumps two or more levels


## Measuring Delays for OPL

- For each primary output, you must check two cases to get the worst-case delay:
- output low

- output high



## 10-Gate Critical Path Delays (FO of 4)

- To determine the performance possible with OPL, we simulated critical paths consisting of 10 gates, each gate in the path driving a load of four identical gates
- We used nominal simulation parameters for the 0.25 micron TSMC process, having a drawn channel length of 0.30 microns


## 10-Gate Critical Path Delays (FO of 4)

- Pull-down nMOS devices for all gates were sized to have an effective width of 2 microns
- pull-down stack of $\boldsymbol{k}$ transistors implies transistor sizes were $2 k$ um
- Static CMOS pMOS transistors were uniformly sized by sweeping their size versus overall delay for the chain of 10 gates
- select the size that minimized the worst case delay for the chain


## 10-Gate Critical Path Delays (FO of 4)

| Chain Type | Static CMOS | OPL-static | OPL-pseudo | OPL-dynamic |
| :---: | :---: | :---: | :---: | :---: |
| INV | $1.62 \mathrm{~ns} \mathrm{(1.0)}$ | 430ps (3.77) | 420ps (3.86) | 430ps (3.77) |
| NOR3 | 3.83ns (1.0) | $1.34 \mathrm{~ns}(2.86)$ | 710ps (5.39) | 760ps (5.04) |
| NAND2 | 2.45ns (1.0) | 940ps (2.61) | 930ps (2.63) | 1.02ns (2.40) |
| NAND3 | 3.32 ns (1.0) | $1.44 \mathrm{~ns}(2.31)$ | $1.54 \mathrm{~ns} \quad(2.16)$ | $1.54 \mathrm{~ns} \mathrm{(2.16)}$ |
| NAND4 | 4.24ns (1.0) | 1.97 ns (2.15) | 2.16ns (1.96) | 2.15ns (1.97) |
| AOI22 | 4.75ns (1.0) | 2.13ns (2.23) | 1.81 ns (2.62) | $1.80 \mathrm{~ns} \mathrm{(2.64)}$ |
| AOI222 | 6.75 ns (1.0) | $3.04 \mathrm{~ns}(2.22)$ | $2.63 \mathrm{~ns}(2.57)$ | 2.49ns (2.71) |
| Average Speedup | (1.0) | (2.59) | (3.03) | (2.96) |

## Energy Consumption

| Chain Type | Static CMOS | OPL-static | OPL-pseudo | OPL-dynamic |
| :---: | :---: | :---: | :---: | :---: |
| INV | 2.00 pJ (1.0) | 3.80 pJ (1.90) | 4.97 pJ (2.49) | 4.41pJ (2.21) |
| NOR3 | 3.19 pJ (1.0) | 4.45 pJ (1.39) | 6.07 pJ (1.90) | 4.47pJ (1.40) |
| NAND2 | 3.83 pJ (1.0) | 5.00 pJ (1.31) | 8.39 pJ (2.19) | 5.60pJ (1.46) |
| NAND3 | 6.23 pJ (1.0) | 6.66 pJ (1.07) | 12.7pJ (2.04) | 7.51pJ (1.21) |
| NAND4 | 8.65 pJ (1.0) | 12.7 pJ (1.47) | 19.3 pJ (2.23) | 10.0pJ (1.16) |
| AOI22 | 6.13 pJ (1.0) | 6.31 pJ (1.03) | 12.8 pJ (2.09) | 7.01pJ (1.14) |
| AOI222 | 7.08 pJ (1.0) | 7.70 pJ (1.09) | 16.7 pJ (2.36) | 8.09pJ (1.14) |
| Average | (1.0) | (1.32) | (2.19) | (1.39) |

## Delays for an 8-Gate (FO of 4) Heterogeneous Critical Path

- NOR3, NAND3, AOI22, INV, INV, NOR3, NAND3, and AOI22
- Having the gates so ordered means that each gate type will have to pull down once and stay high once
- Each gate drives a load of four identical gates
- The device sizes used were exactly those selected for the uniform chains

| Logic Family | Delay | Speedup |
| :---: | :---: | :---: |
| Static CMOS | 2.13 ns | 1.0 |
| OPL-static | 910 ps | 2.34 |
| OPL-pseudo | 650 ps | 3.28 |
| OPL-dynamic | 688 ps | 3.10 |

## Delays for Two Implementations <br> a 32-bit Carry Look-Ahead Adder

| Logic Family | Delay | Speedup | CLA type |
| :--- | :---: | :---: | :--- |
| Static CMOS | 3.0 ns | 1.0 | Three levels |
| OPL-static | 1.5 ns | 2.0 | Three levels |
| OPL-pseudo | 1.8 ns | 1.65 | Three levels |
| OPL-pseudo | 552 ps | 5.43 | Two levels |

- First three designs used all NAND gates; last one is all NOR gates


## OPL Applied to Random Logic

- Early experiments assigned a single clock to all gates in the same level
- At minimum total delay, some gates showed large glitches
- Two methods were used to reduce glitching in selected gates and improve total delay:
- a) Increase pull-up sizes to allow better recovery
- b) Allow more time for (late arriving) inputs to settle. This is done by moving glitching gate back in time by one clock
- Optimized OPL algorithm employs both methods


## Delays for ISCAS Random Logic Benchmarks

| Benchmark <br> (levels) | Static | OPL-Static | OPL-Pseudo |
| :---: | :---: | :---: | :---: |
| t481(7) | $910 \mathrm{ps} \mathrm{(1.0)}$ | $0.46 \mathrm{~ns} \mathrm{(1.98)}$ | $0.430 \mathrm{~ns} \mathrm{(2.12)}$ |
| term1(10) | $1.38 \mathrm{~ns} \mathrm{(1.0)}$ | $0.70 \mathrm{~ns} \mathrm{(1.97)}$ | $0.565 \mathrm{~ns}(2.44)$ |
| x3(10) | $2.58 \mathrm{~ns} \mathrm{(1.0)}$ | $0.67 \mathrm{~ns} \mathrm{(3.85)}$ | $0.537 \mathrm{~ns}(4.80)$ |
| Rot(16) | $2.19 \mathrm{~ns} \mathrm{(1.0)}$ | $1.05 \mathrm{~ns} \mathrm{(2.09)}$ | $1.07 \mathrm{~ns} \mathrm{(2.05)}$ |
| Dalu(14) | $2.35 \mathrm{~ns} \mathrm{(1.0)}$ | $960 \mathrm{ps} \mathrm{(2.45)}$ | $0.857 \mathrm{~ns} \mathrm{(2.73)}$ |
| Average <br> speedup | $(1.0)$ | $(2.47)$ | $(2.82)$ |

- Much higher speed-ups will be obtained when we use a technology mapper specifically for OPL


## Conventional CVSL Gate



## Domino CVSL Gate



## OPL-differential NAND3 Gate



## Delays (ns) for Chains of 10 Gates

| ChainType | Static CMOS | Diff. Domino | OPL-Dynamic | OPL-Diff. |
| :--- | :--- | :--- | :--- | :--- |
| INV | $0.84(1.0)$ | $0.62(0.74)$ | $0.22(0.26)$ | $0.16(0.19)$ |
| NOR2 | $1.26(1.0)$ | $0.66(0.52)$ | $0.30(0.24)$ | $0.25(0.20)$ |
| NOR3 | $1.59(1.0)$ | $0.74(0.47)$ | $0.33(0.21)$ | $0.30(0.19)$ |
| NOR4 | $2.34(1.0)$ | $0.89(0.38)$ | $0.41(0.18)$ | $0.34(0.15)$ |
| NAND2 | $1.02(1.0)$ | $0.66(0.65)$ | $0.46(0.45)$ | $0.30(0.29)$ |
| NAND3 | $1.38(1.0)$ | $0.80(0.58)$ | $0.72(0.52)$ | $0.45(0.33)$ |
| NAND4 | $1.48(1.0)$ | $0.89(0.60)$ | $0.81(0.55)$ | $0.52(0.35)$ |
| AOI21 | $1.30(1.0)$ | $0.72(0.55)$ | $0.41(0.32)$ | $0.35(0.27)$ |
| AOI22 | $1.74(1.0)$ | $0.82(0.47)$ | $0.54(0.31)$ | $0.33(0.19)$ |
| AOI222 | $2.95(1.0)$ | $1.01(0.34)$ | $0.72(0.24)$ | $0.54(0.18)$ |
| AOI31 | $1.76(1.0)$ | $0.83(0.47)$ | $0.55(0.31)$ | $0.52(0.30)$ |
| AOI33 | $2.60(1.0)$ | $1.00(0.38)$ | $0.82(0.32)$ | $0.50(0.19)$ |
| AOI333 | $4.00(1.0)$ | $1.19(0.30)$ | $0.97(0.24)$ | $0.59(0.14)$ |
| AOI321 | $2.43(1.0)$ | $0.91(0.37)$ | $0.55(0.23)$ | $0.54(0.22)$ |
| average | $1.91(1.0)$ | $0.84(0.44)$ | $0.56(0.29)$ | $0.41(0.21)$ |

## Delays (ns) for Chains of 10 Gates with PVT Variations and Clock Skew

- Gaussian distribution of clock separation with 2.5 ? $=30$ ps at .25 micron
- Gaussian distribution of clock separation with 2.5 ? = 15 ps at .18 micron
- Gaussian distribution of channel length with 2.5 ? $=20 \%$ of nominal

| Chain Type | Static CMOS | Diff. Domino | OPL-Dynamic | OPL-Diff. |
| :--- | :--- | :--- | :--- | :--- |
| NOR3 | $1.59 / 1.65$ | $0.62 / 0.80$ | $0.33 / 0.39$ | $0.30 / 0.38$ |
| NAND3 | $1.38 / 1.52$ | $0.80 / 0.87$ | $0.72 / 0.78$ | $0.45 / 0.48$ |
| AOI22 | $1.74 / 1.81$ | $0.82 / 0.85$ | $0.54 / 0.59$ | $0.33 / 0.40$ |
| AOI222 | $2.95 / 3.02$ | $1.01 / 1.06$ | $0.72 / 0.82$ | $0.54 / 0.63$ |
| AOI333 | $4.00 / 4.25$ | $1.19 / 1.24$ | $0.97 / 1.07$ | $0.59 / 0.73$ |
| average | $2.33 / 2.45$ | $0.89 / 0.964$ | $0.66 / 0.73$ | $0.44 / 0.52$ |

## Long Wire With Noise Injection



## Delays of OPL-diff. AOI22 Chains including Coupling Noise.



## Delays of OPL-dyn. AOI22 Chains including Coupling Noise



## Delays of Static CMOS AOI22 Chains including Coupling Noise



## Clock Generation



- A new technique enables the design of a buffer having a delay roughly equal to a FO1 (static) inverter delay!
- Utilizes a novel DLL design
- Given $\mathbf{4 0 \%}$ random variations in L , an average clock separation of 75 ps can be achieved, plus or minus 20 ps
- FO4 for this 0.25 um process is $\mathbf{1 6 4}$ ps


## Simulation Results for Clock Scheme



## Ultra High Speed Adder Design

- Use carry look-ahead since it makes effective use of NOR gates



$\overline{\mathbf{C}_{7}} ? \overline{\overline{\mathbf{g}_{6}} ? \overline{\overline{\mathbf{p}_{6}}} ? \overline{\mathbf{g}_{5}} ? \ldots . . \overline{\overline{\boldsymbol{p}_{6}}} ? \overline{\overline{\mathbf{p}_{5}}} ? \overline{\mathbf{p}_{4}} ? \overline{\mathbf{p}_{3}} ? \overline{\mathbf{p}_{2}} ? \overline{\mathbf{p}_{1}} ? \overline{\mathbf{p}_{0}} ? \overline{\overline{\mathbf{C i n}_{i n}}}}$


## 64-bit Adder Architecture



## 8-Bit Sum using Carry Select



## 64-Bit Adder Results

| 64-bit Adder | Process | Delay | Divided by <br> FO4 Inv Delay |
| :--- | :---: | :---: | :---: |
| OPL | $.25 ? \mathrm{~m}$ | 460 ps | 2.8 |
| David Harris, <br> Stanford | $.6 ? \mathrm{~m}$ |  | 6.4 |
| S.Naffziger, <br> HP | $.5 ? \mathrm{~m}$ | 930 ps | 7.0 |

## 64-bit Adder: Statistical Analysis



## 64-bit Adder: Statistical Analysis



## OPL Summary

- OPL appears to be fastest known logic technique
- Patent application has been filed
- Applicable to: static CMOS, pseudo-nMOS, or dynamic logic
- Speeds up underlying logic family by at least $2 X$
- Developed new, yet faster logic technique - OPL-differential logic (may apply for additional patent)
- OPL 64-bit adder: worst-case delay of 2.8 FO4 INV delays (best previously reported: 6.4-7.0)
- Very applicable to random logic blocks
- Analyzed OPL's performance with respect to PVT variations and coupling noise
- Developed reliable clock generation scheme for OPL circuits
- Intel has a team working on OPL circuit development
- OPL verified for a sub-100nm process

